

SPALLING OF SI SURFACE BY HYDROGEN ELECTROLYTICAL SATURATION AFTER H⁺ IRRADIATION.

Contact Phone

Abstract

The work shows the spalling of single-crystal Si, caused by electrolytic saturation with Hydrogen. Electrolytic saturation of Si samples with Hydrogen was carried out after irradiation with H⁺ ions. The electrolytical saturation by Hydrogen was carried out after irradiation by H⁺ ions. The electrolysis carried out in H₂SO₄ water solution. By electrolytical Hydrogen saturation the Si surface spalling was observed. SEM photos of the samples after irradiation before and after electrolysis confirm that spallation occurs along the layer with the highest hydrogen concentration.

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